

RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFETs

Designed for CDMA base station applications with frequencies from 1930 to 1990 MHz. Can be used in Class AB and Class C for all typical cellular base station modulation formats.

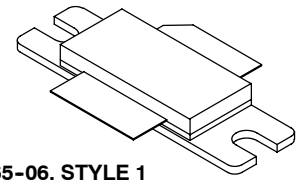
- Typical Single-Carrier W-CDMA Performance: $V_{DD} = 28$ Volts, $I_{DQ} = 1400$ mA, $P_{out} = 63$ Watts Avg., $f = 1987.5$ MHz, IQ Magnitude Clipping, Channel Bandwidth = 3.84 MHz, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF.
 - Power Gain — 20 dB
 - Drain Efficiency — 29%
 - Device Output Signal PAR — 5.9 dB @ 0.01% Probability on CCDF
 - ACPR @ 5 MHz Offset — -33 dBc in 3.84 MHz Channel Bandwidth
- Capable of Handling 5:1 VSWR, @ 32 Vdc, 1960 MHz, 190 Watts CW Output Power (3 dB Input Overdrive from Rated P_{out})
- Typical P_{out} @ 1 dB Compression Point $\approx$ 190 Watts CW

Features

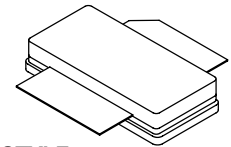
- 100% PAR Tested for Guaranteed Output Power Capability
- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Internally Matched for Ease of Use
- Integrated ESD Protection
- Greater Negative Gate-Source Voltage Range for Improved Class C Operation
- Designed for Digital Predistortion Error Correction Systems
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units, 56 mm Tape Width, 13 inch Reel.

MRF7S19210HR3
MRF7S19210HSR3

1930-1990 MHz, 63 W AVG., 28 V
SINGLE W-CDMA
LATERAL N-CHANNEL
RF POWER MOSFETs



CASE 465-06, STYLE 1
NI-780
MRF7S19210HR3



CASE 465A-06, STYLE 1
NI-780S
MRF7S19210HSR3

Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	-0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	-6.0, +10	Vdc
Operating Voltage	V_{DD}	32, +0	Vdc
Storage Temperature Range	T_{stg}	-65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature (1,2)	T_J	225	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value (2,3)	Unit
Thermal Resistance, Junction to Case Case Temperature 85°C, 190 W CW Case Temperature 79°C, 63 W CW	$R_{\theta JC}$	0.34 0.38	°C/W

1. Continuous use at maximum temperature will affect MTTF.
2. MTTF calculator available at <http://www.freescale.com/rf>. Select Software & Tools/Development Tools/Calculators to access MTTF calculators by product.
3. Refer to AN1955, *Thermal Measurement Methodology of RF Power Amplifiers*. Go to <http://www.freescale.com/rf>. Select Documentation/Application Notes - AN1955.

Table 3. ESD Protection Characteristics

Test Methodology	Class
Human Body Model (per JESD22-A114)	1C (Minimum)
Machine Model (per EIA/JESD22-A115)	A (Minimum)
Charge Device Model (per JESD22-C101)	IV (Minimum)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
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Off Characteristics

Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc

On Characteristics

Gate Threshold Voltage ($V_{DS} = 10\text{ Vdc}$, $I_D = 513\text{ }\mu\text{Adc}$)	$V_{GS(th)}$	1.2	2	2.7	Vdc
Gate Quiescent Voltage ($V_{DS} = 28\text{ Vdc}$, $I_D = 1400\text{ mAdc}$)	$V_{GS(Q)}$	—	2.7	—	Vdc
Fixture Gate Quiescent Voltage ⁽¹⁾ ($V_{DD} = 28\text{ Vdc}$, $I_D = 1400\text{ mAdc}$, Measured in Functional Test)	$V_{GG(Q)}$	4	5.4	7	Vdc
Drain-Source On-Voltage ($V_{GS} = 10\text{ Vdc}$, $I_D = 5.13\text{ Adc}$)	$V_{DS(on)}$	0.1	0.2	0.3	Vdc

Dynamic Characteristics ⁽²⁾

Reverse Transfer Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{rss}	—	2.17	—	pF
Output Capacitance ($V_{DS} = 28\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{oss}	—	257	—	pF
Input Capacitance ($V_{DS} = 28\text{ Vdc}$, $V_{GS} = 0\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz)	C_{iss}	—	508	—	pF

Functional Tests (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1400\text{ mA}$, $P_{out} = 63\text{ W Avg.}$, $f = 1987.5\text{ MHz}$, Single-Carrier W-CDMA, IQ Magnitude Clipping, Input Signal PAR = 7.5 dB @ 0.01% Probability on CCDF. ACPR measured in 3.84 MHz Channel Bandwidth @ $\pm 5\text{ MHz}$ Offset.

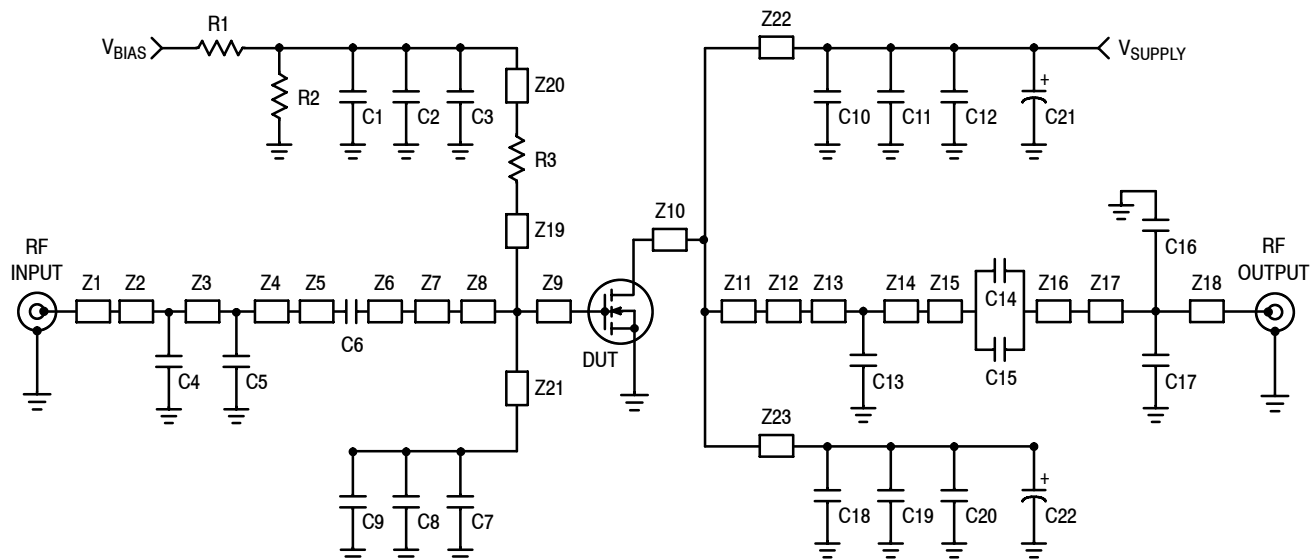
Power Gain	G_{ps}	18	20	21.5	dB
Drain Efficiency	η_D	26	29	—	%
Output Peak-to-Average Ratio @ 0.01% Probability on CCDF	PAR	5.5	5.9	—	dB
Adjacent Channel Power Ratio	ACPR	—	-33	-31	dBc
Input Return Loss	IRL	—	-9.5	-6	dB

- $V_{GG} = 2 \times V_{GS(Q)}$. Parameter measured on Freescale Test Fixture, due to resistive divider network on the board. Refer to Test Circuit schematic.
- Part internally matched both on input and output.

(continued)

Table 4. Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted) **(continued)**

Characteristic	Symbol	Min	Typ	Max	Unit
Typical Performances (In Freescale Test Fixture, 50 ohm system) $V_{DD} = 28\text{ Vdc}$, $I_{DQ} = 1400\text{ mA}$, 1930–1990 MHz Bandwidth					
IMD Symmetry @ 160 W PEP, P_{out} where IMD Third Order Intermodulation $\cong 30\text{ dBc}$ (Delta IMD Third Order Intermodulation between Upper and Lower Sidebands $> 2\text{ dB}$)	IMD_{sym}	—	15	—	MHz
VBW Resonance Point (IMD Third Order Intermodulation Inflection Point)	VBW_{res}	—	50	—	MHz
Gain Flatness in 60 MHz Bandwidth @ $P_{out} = 63\text{ W Avg.}$	G_F	—	0.9	—	dB
Average Deviation from Linear Phase in 60 MHz Bandwidth @ $P_{out} = 190\text{ W CW}$	Φ	—	0.95	—	°
Average Group Delay @ $P_{out} = 190\text{ W CW}$, $f = 1960\text{ MHz}$	Delay	—	2.82	—	ns
Part-to-Part Insertion Phase Variation @ $P_{out} = 190\text{ W CW}$, $f = 1960\text{ MHz}$, Six Sigma Window	$\Delta\Phi$	—	28.9	—	°
Gain Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔG	—	0.019	—	dB/°C
Output Power Variation over Temperature (-30°C to $+85^\circ\text{C}$)	ΔP_{1dB}	—	0.008	—	dB/°C



Z1	0.126" x 0.066" Microstrip	Z13	0.078" x 0.102" Microstrip
Z2	0.584" x 0.079" Microstrip	Z14	0.319" x 0.102" Microstrip
Z3	0.110" x 0.079" Microstrip	Z15	0.709" x 0.220" Microstrip
Z4	0.133" x 0.079" Microstrip	Z16	0.709" x 0.220" Microstrip
Z5	0.059" x 0.118" Microstrip	Z17	0.747" x 0.066" Microstrip
Z6	0.059" x 0.118" Microstrip	Z18	0.227" x 0.066" Microstrip
Z7	0.197" x 0.102" Microstrip	Z19	0.145" x 0.090" Microstrip
Z8	0.860" x 0.551" Microstrip	Z20	0.548" x 0.090" Microstrip
Z9	0.114" x 0.551" Microstrip	Z21	0.734" x 0.090" Microstrip
Z10	0.129" x 1.102" Microstrip	Z22, Z23	1.044" x 0.100" Microstrip
Z11	0.304" x 1.102" Microstrip	PCB	Taconic RF35, 0.030", $\epsilon_r = 3.5$
Z12	0.295" x 0.276" Microstrip		

Figure 1. MRF7S19210HR3(HSR3) Test Circuit Schematic

Table 5. MRF7S19210HR3(HSR3) Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
C1, C9, C11, C12, C19, C20	10 μ F, 50 V Chip Capacitors	C5750X5R1H106M	TDK
C2, C8	100 nF Chip Capacitors	12065C104KAT2A	AVX
C3, C6, C7, C10, C14, C15, C18	8.2 pF Chip Capacitors	ATC100B8R2BT500XT	ATC
C4	0.2 pF Chip Capacitor	ATC100B0R2BT500XT	ATC
C5	1.8 pF Chip Capacitor	ATC100B1R8BT500XT	ATC
C13	0.4 pF Chip Capacitor	ATC100B0R4BT500XT	ATC
C16, C17	0.5 pF Chip Capacitors	ATC100B0R5BT500XT	ATC
C21, C22	470 μ F Electrolytic Capacitors	222212018471	Vishay BC Components
R1, R2	10 k Ω , 1/4 W Chip Resistors	WCR120610KFI	Welwyn
R3	10 Ω , 1/4 W Chip Resistor	WCR120610RFI	Welwyn

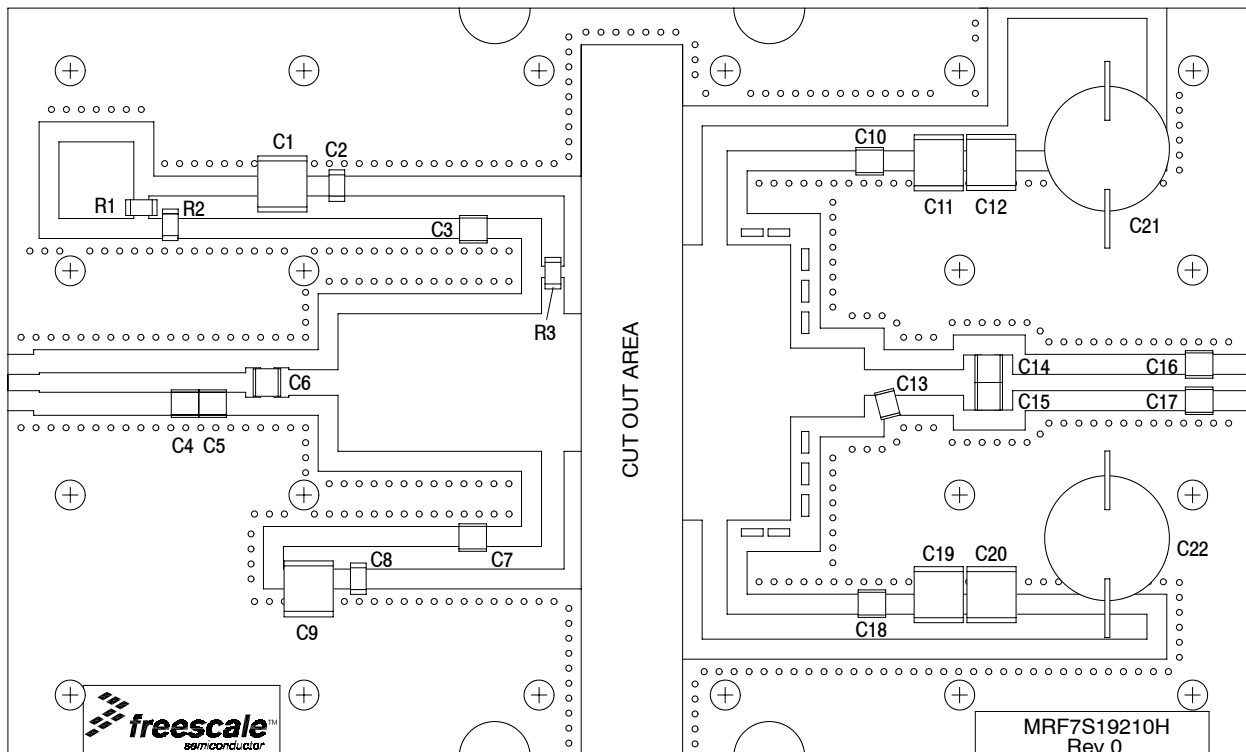


Figure 2. MRF7S19210HR3(HSR3) Test Circuit Component Layout

TYPICAL CHARACTERISTICS

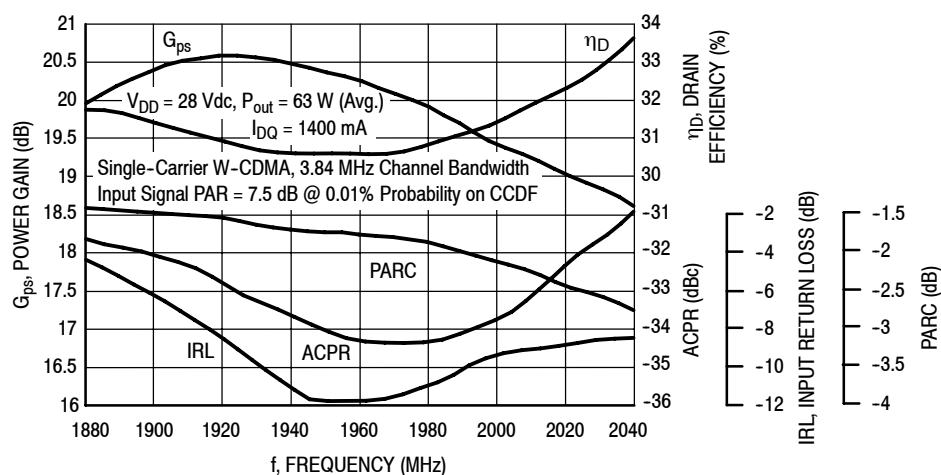


Figure 3. Output Peak-to-Average Ratio Compression (PARC) Broadband Performance @ $P_{out} = 63$ Watts Avg.

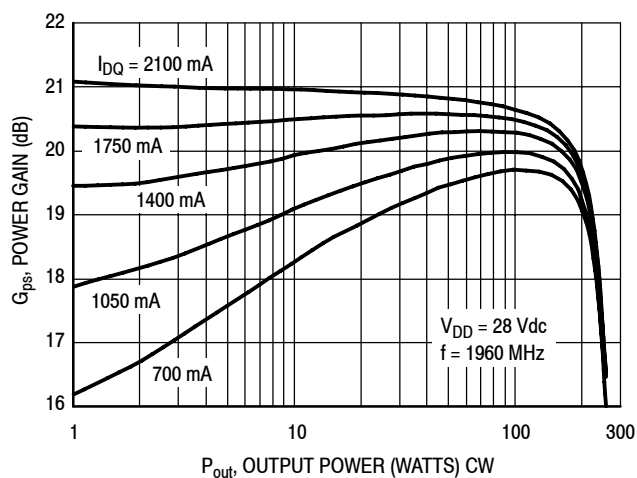


Figure 4. Power Gain versus Output Power

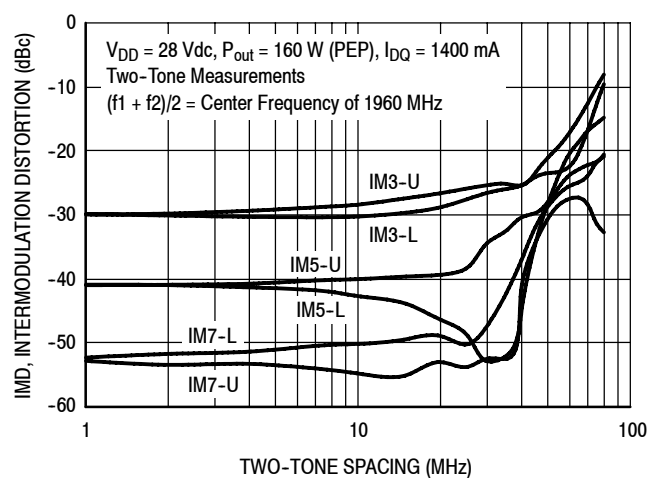


Figure 5. Intermodulation Distortion Products versus Two-Tone Spacing

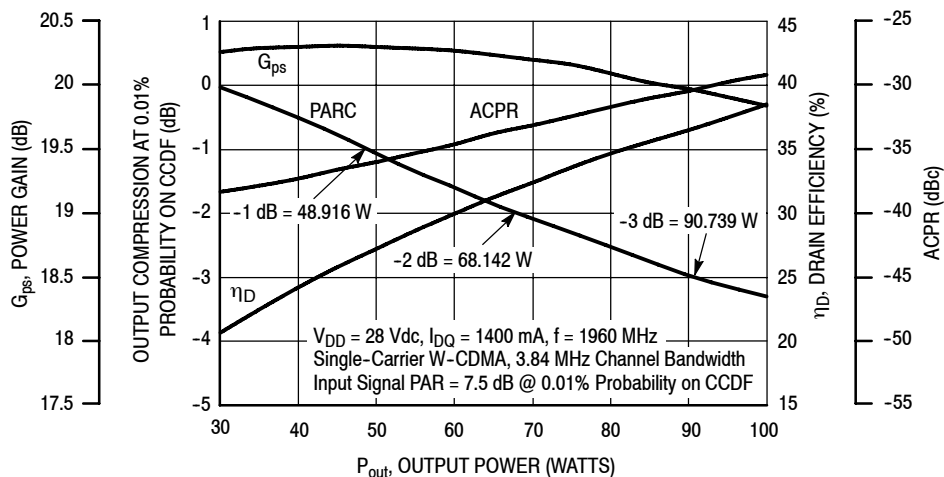


Figure 6. Output Peak-to-Average Ratio Compression (PARC) versus Output Power

TYPICAL CHARACTERISTICS

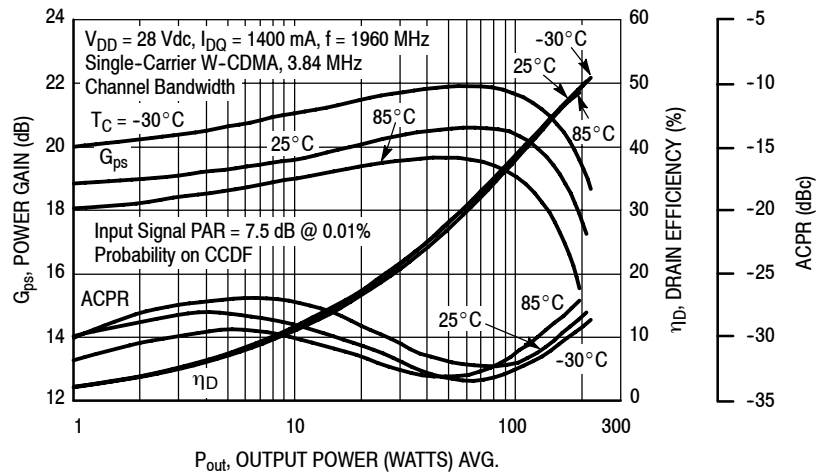


Figure 7. Single-Carrier W-CDMA Power Gain, Drain Efficiency and ACPR versus Output Power

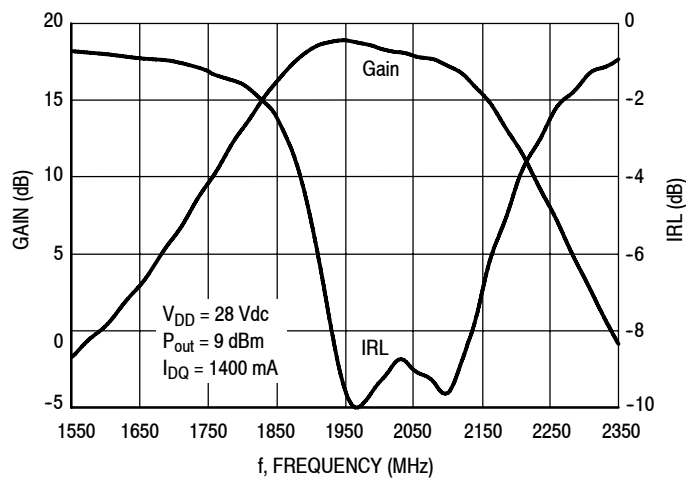


Figure 8. Broadband Frequency Response

W-CDMA TEST SIGNAL

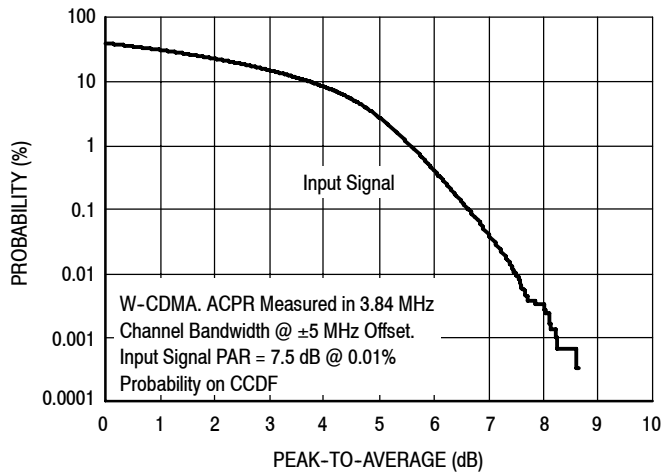


Figure 9. CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal

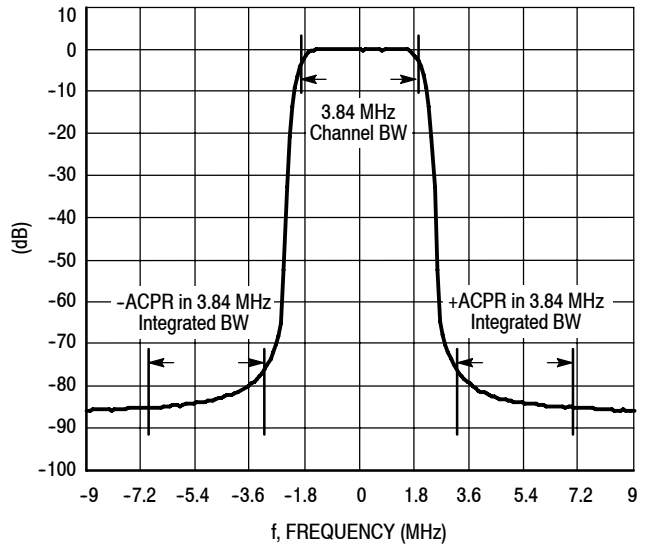
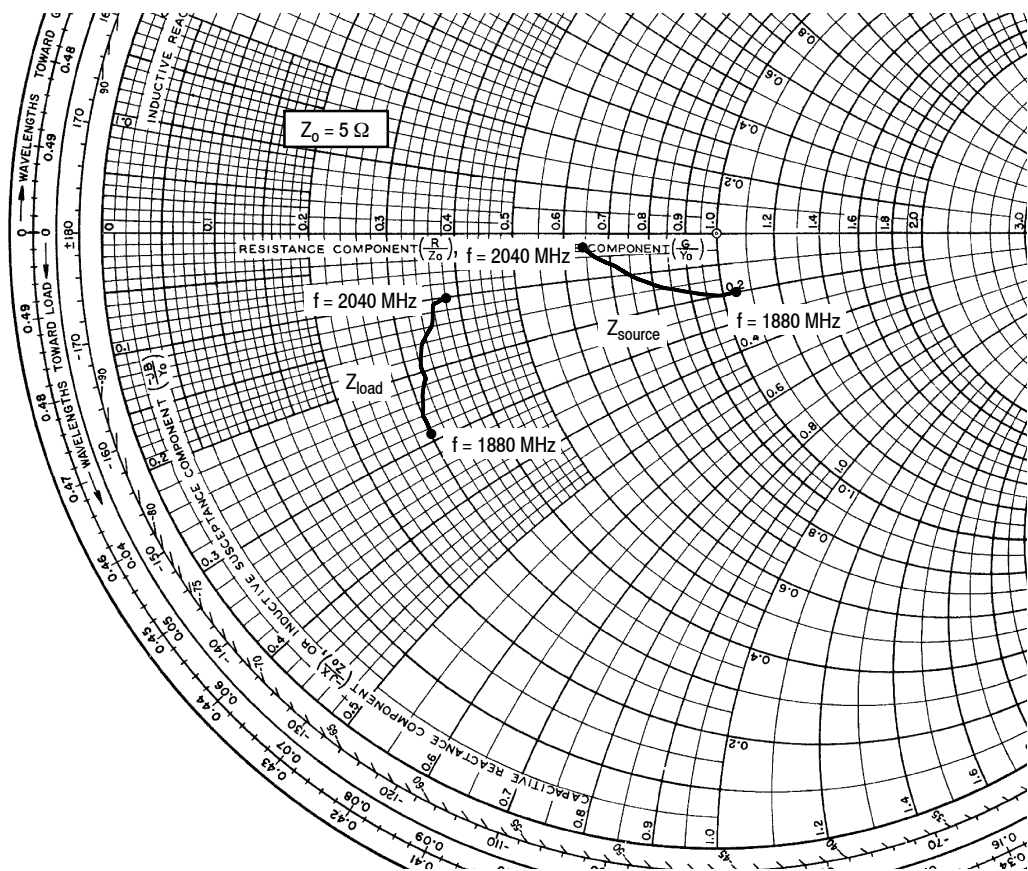


Figure 10. Single-Carrier W-CDMA Spectrum



$V_{DD} = 28 \text{ Vdc}$, $I_{DQ} = 1400 \text{ mA}$, $P_{out} = 63 \text{ W Avg.}$

f MHz	Z_{source} Ω	Z_{load} Ω
1880	$5.20 - j1.02$	$1.49 - j1.45$
1900	$4.90 - j1.00$	$1.52 - j1.30$
1920	$4.60 - j0.92$	$1.55 - j1.16$
1940	$4.31 - j0.82$	$1.58 - j1.04$
1960	$4.04 - j0.71$	$1.61 - j0.93$
1980	$3.80 - j0.56$	$1.66 - j0.82$
2000	$3.58 - j0.42$	$1.73 - j0.70$
2020	$3.38 - j0.30$	$1.81 - j0.57$
2040	$3.19 - j0.16$	$1.88 - j0.49$

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.

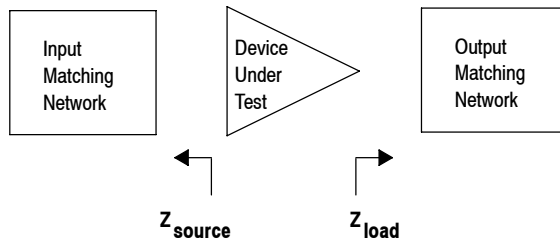
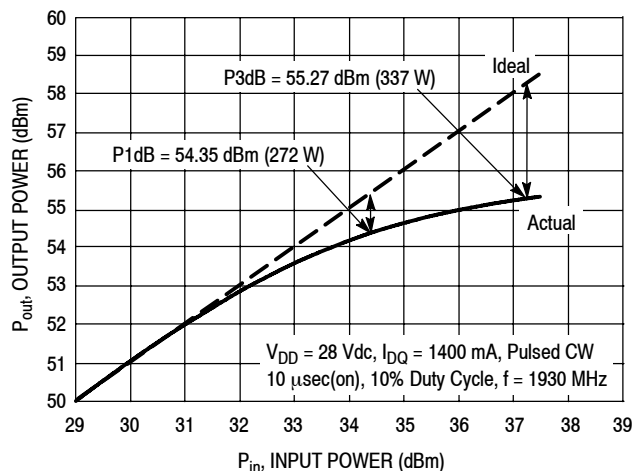


Figure 11. Series Equivalent Source and Load Impedance

ALTERNATIVE PEAK TUNE LOAD PULL CHARACTERISTICS

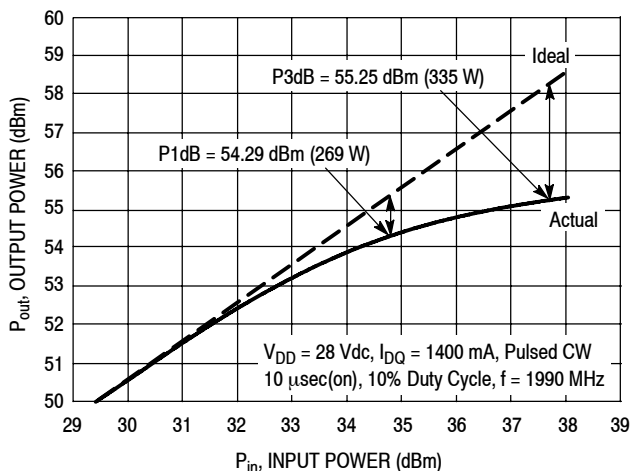


NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

Test Impedances per Compression Level

	Z_{source} Ω	Z_{load} Ω
P1dB	$5.72 - j5.51$	$1.30 - j0.69$

Figure 12. Pulsed CW Output Power versus Input Power @ 28 V @ 1930 MHz



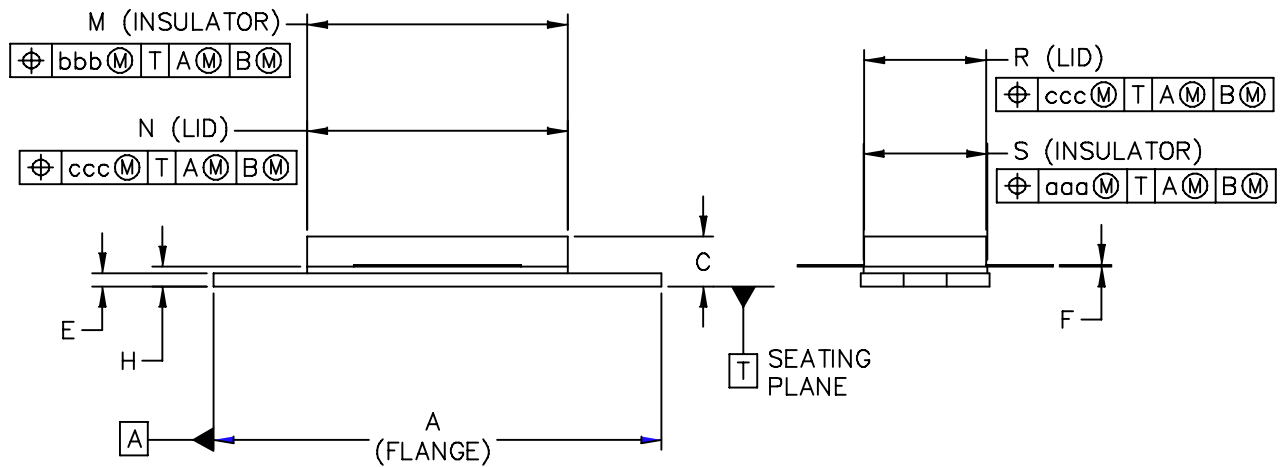
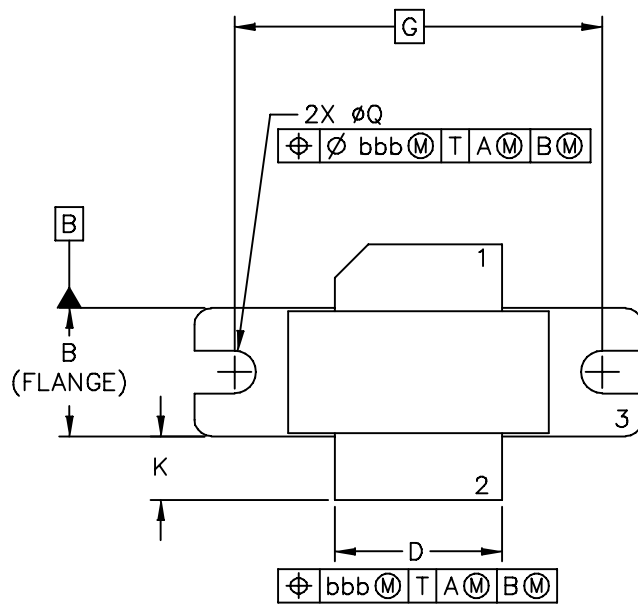
NOTE: Load Pull Test Fixture Tuned for Peak P1dB Output Power @ 28 V

Test Impedances per Compression Level

	Z_{source} Ω	Z_{load} Ω
P1dB	$6.20 + j1.19$	$1.09 - j0.46$

Figure 13. Pulsed CW Output Power versus Input Power @ 28 V @ 1990 MHz

PACKAGE DIMENSIONS



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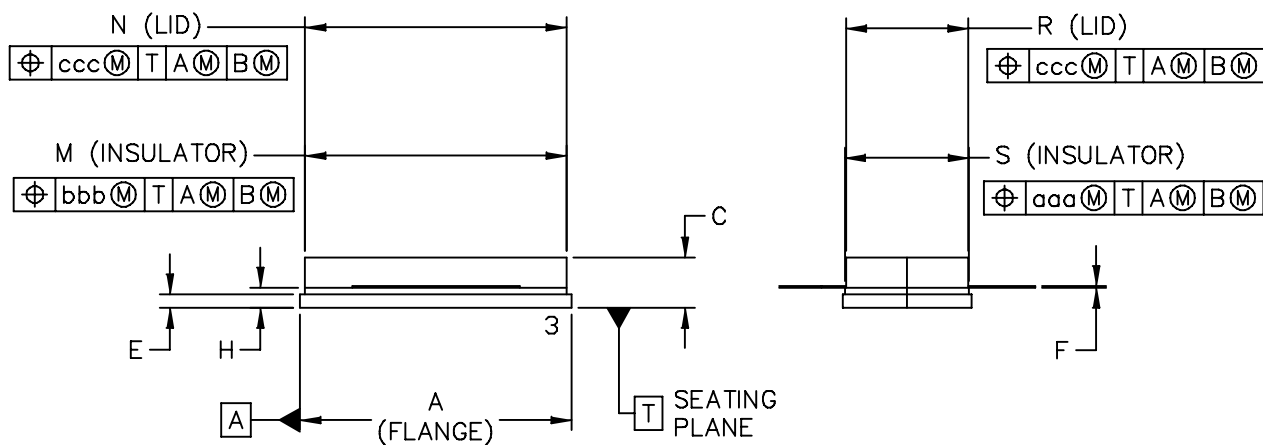
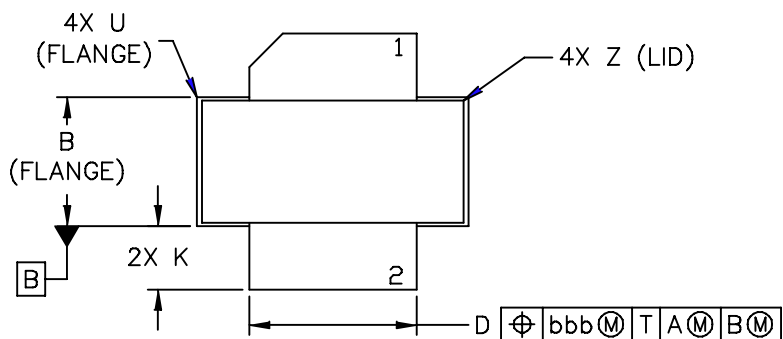
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2. CONTROLLING DIMENSION: INCH.
3. DELETED
4. DIMENSION H IS MEASURED .030 (.762) AWAY FROM PACKAGE BODY.

STYLE 1:

- PIN 1. DRAIN
2. GATE
3. SOURCE

INCH		MILLIMETER		INCH		MILLIMETER	
DIM	MIN	MAX	MIN	MAX	DIM	MIN	MAX
A	1.335	1.345	33.91	34.16	R	.365	.375
B	.380	.390	9.65	9.91	S	.365	.375
C	.125	.170	3.18	4.32	aaa	.005	
D	.495	.505	12.57	12.83	bbb	.010	
E	.035	.045	0.89	1.14	ccc	.015	
F	.003	.006	0.08	0.15			
G	1.100 BSC		27.94 BSC				
H	.057	.067	1.45	1.7			
K	.170	.210	4.32	5.33			
M	.774	.786	19.66	19.96			
N	.772	.788	19.6	20			
Q	ø.118	ø.138	ø3	ø3.51			
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STYLE 1:

- PIN 1. DRAIN
2. GATE
3. SOURCE

DIM	INCH		MILLIMETER		DIM	INCH		MILLIMETER	
	MIN	MAX	MIN	MAX		MIN	MAX	MIN	MAX
A	.805	— .815	20.45	— 20.7	U	—	— .040	—	— 1.02
B	.380	— .390	9.65	— 9.91	Z	—	— .030	—	— 0.76
C	.125	— .170	3.18	— 4.32	aaa	—	.005 —	—	0.127 —
D	.495	— .505	12.57	— 12.83	bbb	—	.010 —	—	0.254 —
E	.035	— .045	0.89	— 1.14	ccc	—	.015 —	—	0.381 —
F	.003	— .006	0.08	— 0.15	—	—	— —	—	— —
H	.057	— .067	1.45	— 1.7	—	—	— —	—	— —
K	.170	— .210	4.32	— 5.33	—	—	— —	—	— —
M	.774	— .786	19.61	— 20.02	—	—	— —	—	— —
N	.772	— .788	19.61	— 20.02	—	—	— —	—	— —
R	.365	— .375	9.27	— 9.53	—	—	— —	—	— —
S	.365	— .375	9.27	— 9.52	—	—	— —	—	— —
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					CASE NUMBER: 465A—06			31 MAR 2005	
					STANDARD: NON—JEDEC				

PRODUCT DOCUMENTATION AND SOFTWARE

Refer to the following documents and software to aid your design process.

Application Notes

- AN1955: Thermal Measurement Methodology of RF Power Amplifiers

Engineering Bulletins

- EB212: Using Data Sheet Impedances for RF LDMOS Devices

Software

- Electromigration MTTF Calculator
- RF High Power Model

For Software, do a Part Number search at <http://www.freescale.com>, and select the “Part Number” link. Go to the Software & Tools tab on the part’s Product Summary page to download the respective tool.

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
0	Dec. 2008	• Initial Release of Data Sheet
1	Mar. 2011	• Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN13628, p. 1, 2 • Fig. 9, MTTF versus Junction Temperature removed, p. 7. Refer to the device’s MTTF Calculator available at freescale.com/RFpower. Go to Design Resources > Software and Tools. • Fig. 10, CCDF W-CDMA IQ Magnitude Clipping, Single-Carrier Test Signal and Fig. 11, Single-Carrier W-CDMA Spectrum updated to show the undistorted input test signal, p. 8 (renumbered as Figs. 9 and 10 respectively after Fig. 9 removed) • Added Electromigration MTTF Calculator and RF High Power Model availability to Product Software, p. 15

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